

74LVC2G240

Dual inverting buffer/line driver; 3-state

Rev. 03 — 5 October 2007

Product data sheet

1. General description

The 74LVC2G240 is a dual inverting buffer/line driver with 3-state outputs. The 3-state outputs are controlled by the output enable inputs $\overline{1OE}$ and $\overline{2OE}$. A HIGH level at pins $n\overline{OE}$ causes outputs to assume a high-impedance OFF-state. Schmitt trigger action at all inputs makes the circuit highly tolerant of slower input rise and fall times.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- ± 24 mA output drive ($VCC = 3.0$ V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from -40 °C to $+85$ °C and -40 °C to $+125$ °C

3. Ordering information

Table 1. Ordering information

Type number	Package				Version
	Temperature range	Name	Description		
74LVC2G240DP	−40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm		SOT505-2
74LVC2G240DC	−40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm		SOT765-1
74LVC2G240GT	−40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm		SOT833-1
74LVC2G240GM	−40 °C to +125 °C	XQFN8	plastic extremely thin quad flat package; no leads; 8 terminals; body 1.6 × 1.6 × 0.5 mm		SOT902-1

4. Marking

Table 2. Marking

Type number	Marking code
74LVC2G240DP	V240
74LVC2G240DC	V40
74LVC2G240GT	V40
74LVC2G240GM	V40

5. Functional diagram

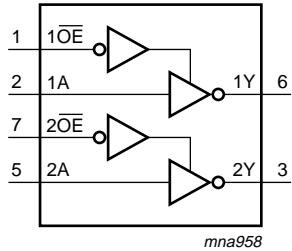


Fig 1. Logic symbol

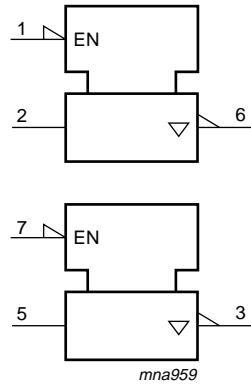


Fig 2. IEC logic symbol

6. Pinning information

6.1 Pinning

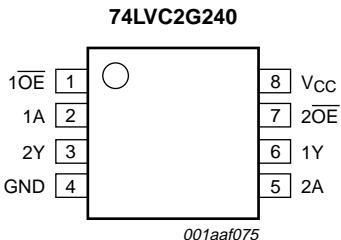


Fig 3. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)

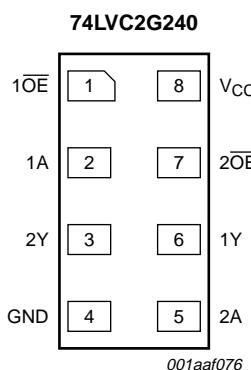


Fig 4. Pin configuration SOT833-1 (XSON8)

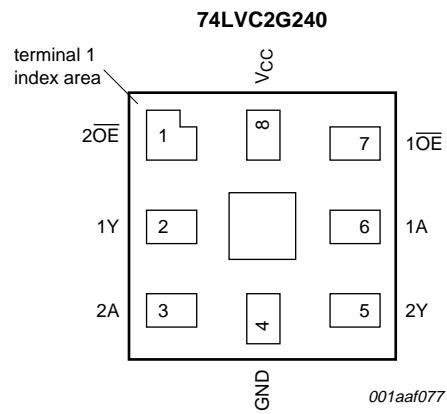


Fig 5. Pin configuration SOT902-1 (XQFN8)

6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT505-2, SOT765-1, SOT833-1	SOT902-1	
$\overline{1OE}$	1	7	output enable input $\overline{1OE}$ (active LOW)
1A	2	6	data input
2Y	3	5	data output
GND	4	4	ground (0 V)
2A	5	3	data input
1Y	6	2	data output
$\overline{2OE}$	7	1	output enable input $\overline{2OE}$ (active LOW)
V _{CC}	8	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Input		Output
nOE	nA	nY
L	L	H
L	H	L
H	X	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
V _I	input voltage		^[1] -0.5	+6.5	V
I _{OK}	output clamping current	V _O > V _{CC} or V _O < 0 V	-	±50	mA
V _O	output voltage	enable mode	^{[1][2]} -0.5	V _{CC} + 0.5	V
		disable mode	^{[1][2]} -0.5	+6.5	V
		Power-down mode	^{[1][2]} -0.5	+6.5	V
I _O	output current	V _O = 0 V to V _{CC}	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	^[3] -	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When V_{CC} = 0 V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For TSSOP8 packages: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.

For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K.

For XSON8 and XQFN8 packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CC}	supply voltage		1.65	-	5.5	V
V _I	input voltage		0	-	5.5	V
V _O	output voltage	V _{CC} = 1.65 V to 5.5 V; enable mode	0	-	V _{CC}	V
		V _{CC} = 1.65 V to 5.5 V; disable mode	0	-	5.5	V
		V _{CC} = 0 V; Power-down mode	0	-	5.5	V
T _{amb}	ambient temperature		-40	-	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 1.65 V to 2.7 V	-	-	20	ns/V
		V _{CC} = 2.7 V to 5.5 V	-	-	10	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = -40 °C to +85 °C^[1]						
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V _{CC} = 4.5 V to 5.5 V	0.7V _{CC}	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	0.35V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	0.3V _{CC}	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 100 μA; V _{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.45	V
		I _O = 8 mA; V _{CC} = 2.3 V	-	-	0.3	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.4	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.55	V
		I _O = 32 mA; V _{CC} = 4.5 V	-	-	0.55	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -100 μA; V _{CC} = 1.65 V to 5.5 V	V _{CC} - 0.1	-	-	V
		I _O = -4 mA; V _{CC} = 1.65 V	1.2	-	-	V
		I _O = -8 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I _O = -12 mA; V _{CC} = 2.7 V	2.2	-	-	V
		I _O = -24 mA; V _{CC} = 3.0 V	2.3	-	-	V
		I _O = -32 mA; V _{CC} = 4.5 V	3.8	-	-	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	±0.1	±5	μA

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = 5.5$ V or GND; $V_{CC} = 3.6$ V	-	± 0.1	± 10	μA
I_{OFF}	power-off leakage current	V_I or $V_O = 5.5$ V; $V_{CC} = 0$ V	-	± 0.1	± 10	μA
I_{CC}	supply current	$V_I = 5.5$ V or GND; $I_O = 0$ A; $V_{CC} = 1.65$ V to 5.5 V	-	0.1	10	μA
ΔI_{CC}	additional supply current	per pin; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 2.3$ V to 5.5 V	-	5	500	μA
C_I	input capacitance		-	2	-	pF
$T_{amb} = -40$ °C to +125 °C						
V_{IH}	HIGH-level input voltage	$V_{CC} = 1.65$ V to 1.95 V	$0.65V_{CC}$	-	-	V
		$V_{CC} = 2.3$ V to 2.7 V	1.7	-	-	V
		$V_{CC} = 2.7$ V to 3.6 V	2.0	-	-	V
		$V_{CC} = 4.5$ V to 5.5 V	$0.7V_{CC}$	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 1.65$ V to 1.95 V	-	-	$0.35V_{CC}$	V
		$V_{CC} = 2.3$ V to 2.7 V	-	-	0.7	V
		$V_{CC} = 2.7$ V to 3.6 V	-	-	0.8	V
		$V_{CC} = 4.5$ V to 5.5 V	-	-	$0.3V_{CC}$	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 100 \mu A$; $V_{CC} = 1.65$ V to 5.5 V	-	-	0.1	V
		$I_O = 4$ mA; $V_{CC} = 1.65$ V	-	-	0.70	V
		$I_O = 8$ mA; $V_{CC} = 2.3$ V	-	-	0.45	V
		$I_O = 12$ mA; $V_{CC} = 2.7$ V	-	-	0.60	V
		$I_O = 24$ mA; $V_{CC} = 3.0$ V	-	-	0.80	V
		$I_O = 32$ mA; $V_{CC} = 4.5$ V	-	-	0.80	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -100 \mu A$; $V_{CC} = 1.65$ V to 5.5 V	$V_{CC} - 0.1$	-	-	V
		$I_O = -4$ mA; $V_{CC} = 1.65$ V	0.95	-	-	V
		$I_O = -8$ mA; $V_{CC} = 2.3$ V	1.7	-	-	V
		$I_O = -12$ mA; $V_{CC} = 2.7$ V	1.9	-	-	V
		$I_O = -24$ mA; $V_{CC} = 3.0$ V	2.0	-	-	V
		$I_O = -32$ mA; $V_{CC} = 4.5$ V	3.4	-	-	V
I_I	input leakage current	$V_I = 5.5$ V or GND; $V_{CC} = 0$ V to 5.5 V	-	-	± 20	μA
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = 5.5$ V or GND; $V_{CC} = 3.6$ V	-	-	± 20	μA
I_{OFF}	power-off leakage current	V_I or $V_O = 5.5$ V; $V_{CC} = 0$ V	-	-	± 20	μA
I_{CC}	supply current	$V_I = 5.5$ V or GND; $I_O = 0$ A; $V_{CC} = 1.65$ V to 5.5 V	-	-	40	μA
ΔI_{CC}	additional supply current	per pin; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 2.3$ V to 5.5 V	-	-	5	mA

[1] Typical values are measured at $V_{CC} = 3.3$ V and $T_{amb} = 25$ °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground 0 V); for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{pd}	propagation delay	nA to nY; see Figure 6	^[2]					
		V _{CC} = 1.65 V to 1.95 V	1.0	4.1	9.5	1.0	11.9	ns
		V _{CC} = 2.3 V to 2.7 V	0.5	2.6	5.2	0.5	6.5	ns
		V _{CC} = 2.7 V	1.0	3.0	5.5	1.0	6.9	ns
		V _{CC} = 3.0 V to 3.6 V	0.5	2.5	4.6	0.5	5.8	ns
t _{en}	enable time	nOE to nY; see Figure 7	^[3]					
		V _{CC} = 1.65 V to 1.95 V	1.5	4.5	10.3	1.5	12.9	ns
		V _{CC} = 2.3 V to 2.7 V	1.0	2.9	5.6	1.0	7.0	ns
		V _{CC} = 2.7 V	1.5	3.4	5.6	1.5	7.0	ns
		V _{CC} = 3.0 V to 3.6 V	0.5	2.5	4.7	0.5	5.9	ns
t _{dis}	disable time	nOE to nY; see Figure 7	^[4]					
		V _{CC} = 1.65 V to 1.95 V	1.0	3.5	11.6	1.0	14.1	ns
		V _{CC} = 2.3 V to 2.7 V	0.5	1.9	5.8	0.5	7.6	ns
		V _{CC} = 2.7 V	1.0	2.8	4.5	1.0	5.8	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	2.7	4.4	1.0	5.7	ns
C _{PD}	power dissipation capacitance	per buffer; V _I = GND to V _{CC}	^[5]					
		output enabled	-	18	-	-	-	pF
		output disabled	-	5	-	-	-	pF

[1] Typical values are measured at nominal V_{CC} and at T_{amb} = 25 °C.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}

[3] t_{en} is the same as t_{PZH} and t_{PZL}

[4] t_{dis} is the same as t_{PLZ} and t_{PHZ}

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

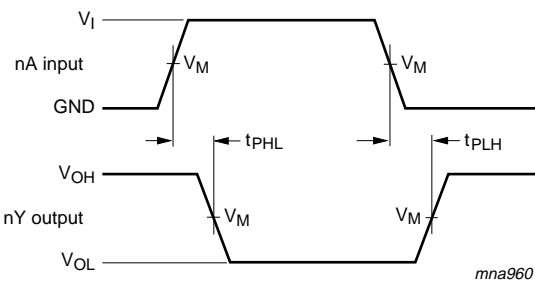
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$$\Sigma(C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs.}$$

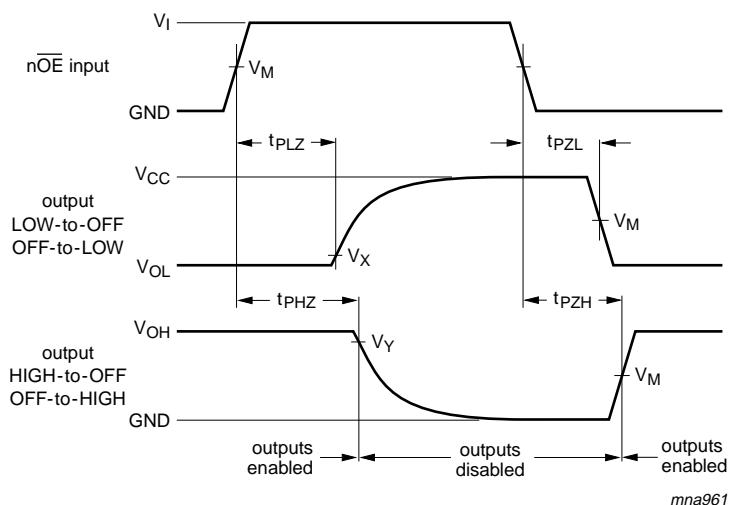
12. Waveforms



Measurement points are given in [Table 9](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 6. The data input (nA) to output (nY) propagation delays



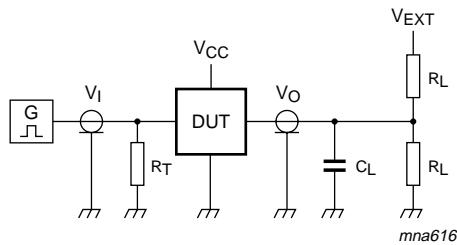
Measurement points are given in [Table 9](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 7. Enable and disable times

Table 9. Measurement points

Supply voltage	Input	Output		
V_{CC}	V_M	V_M	V_X	V_Y
1.65 V to 1.95 V	0.5 V_{CC}	0.5 V_{CC}	$V_{OL} + 0.15$ V	$V_{OH} - 0.15$ V
2.3 V to 2.7 V	0.5 V_{CC}	0.5 V_{CC}	$V_{OL} + 0.15$ V	$V_{OH} - 0.15$ V
2.7 V	1.5 V	1.5 V	$V_{OL} + 0.3$ V	$V_{OH} - 0.3$ V
3.0 V to 3.6 V	1.5 V	1.5 V	$V_{OL} + 0.3$ V	$V_{OH} - 0.3$ V
4.5 V to 5.5 V	0.5 V_{CC}	0.5 V_{CC}	$V_{OL} + 0.3$ V	$V_{OH} - 0.3$ V



Test data is given in [Table 10](#).

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

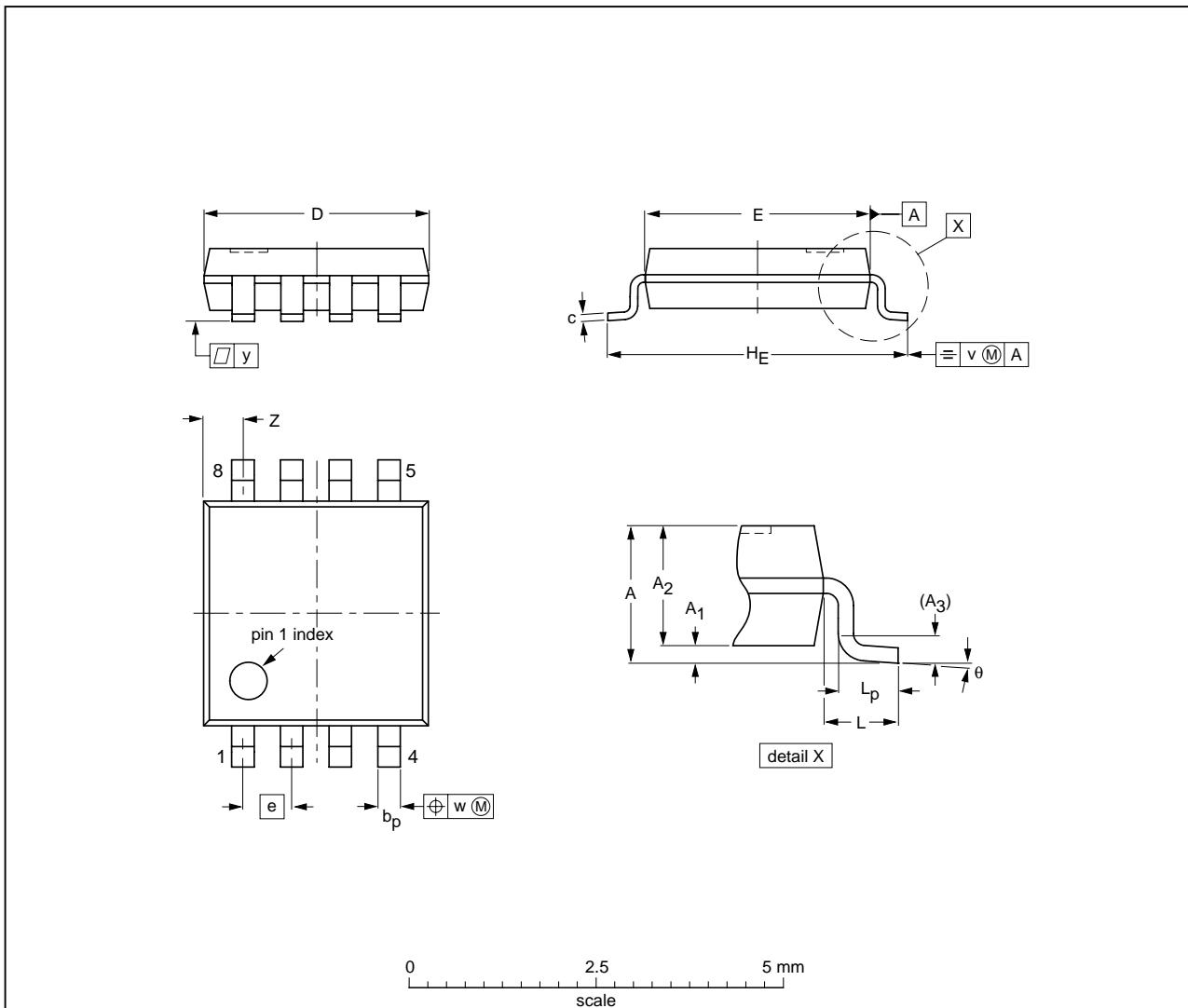
Fig 8. Load circuitry for switching times

Table 10. Test data

Supply voltage	Input	Load		V_{EXT}		
		V_I	C_L	R_L	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}
1.65 V to 1.95 V	V_{CC}	30 pF	1 k Ω	open	GND	$2 \times V_{CC}$
2.3 V to 2.7 V	V_{CC}	30 pF	500 Ω	open	GND	$2 \times V_{CC}$
2.7 V	2.7 V	50 pF	500 Ω	open	GND	6 V
3.0 V to 3.6 V	2.7 V	50 pF	500 Ω	open	GND	6 V
4.5 V to 5.5 V	V_{CC}	50 pF	500 Ω	open	GND	$2 \times V_{CC}$

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	v	w	y	Z ⁽¹⁾	θ
mm	1.1	0.15 0.00	0.95 0.75	0.25	0.38 0.22	0.18 0.08	3.1 2.9	3.1 2.9	0.65	4.1 3.9	0.5	0.47 0.33	0.2	0.13	0.1	0.70 0.35	8° 0°

Note

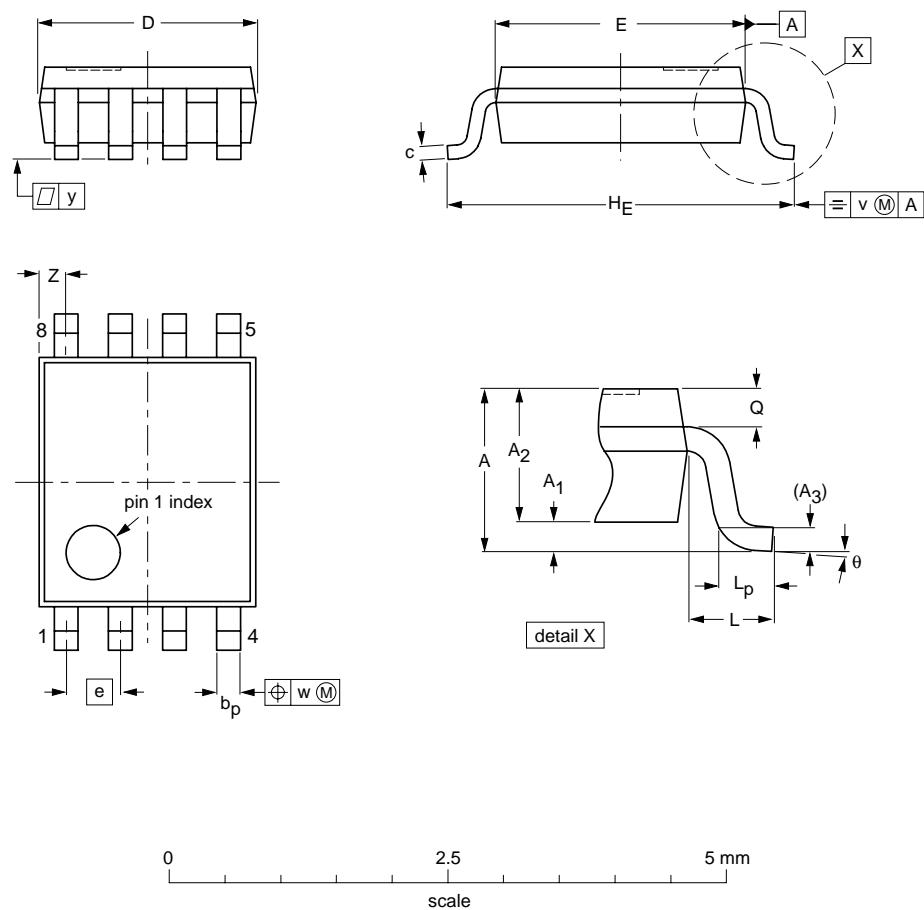
- Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT505-2		---				02-01-16

Fig 9. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

**DIMENSIONS (mm are the original dimensions)**

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽²⁾	e	H _E	L	L _p	Q	v	w	y	z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

Notes

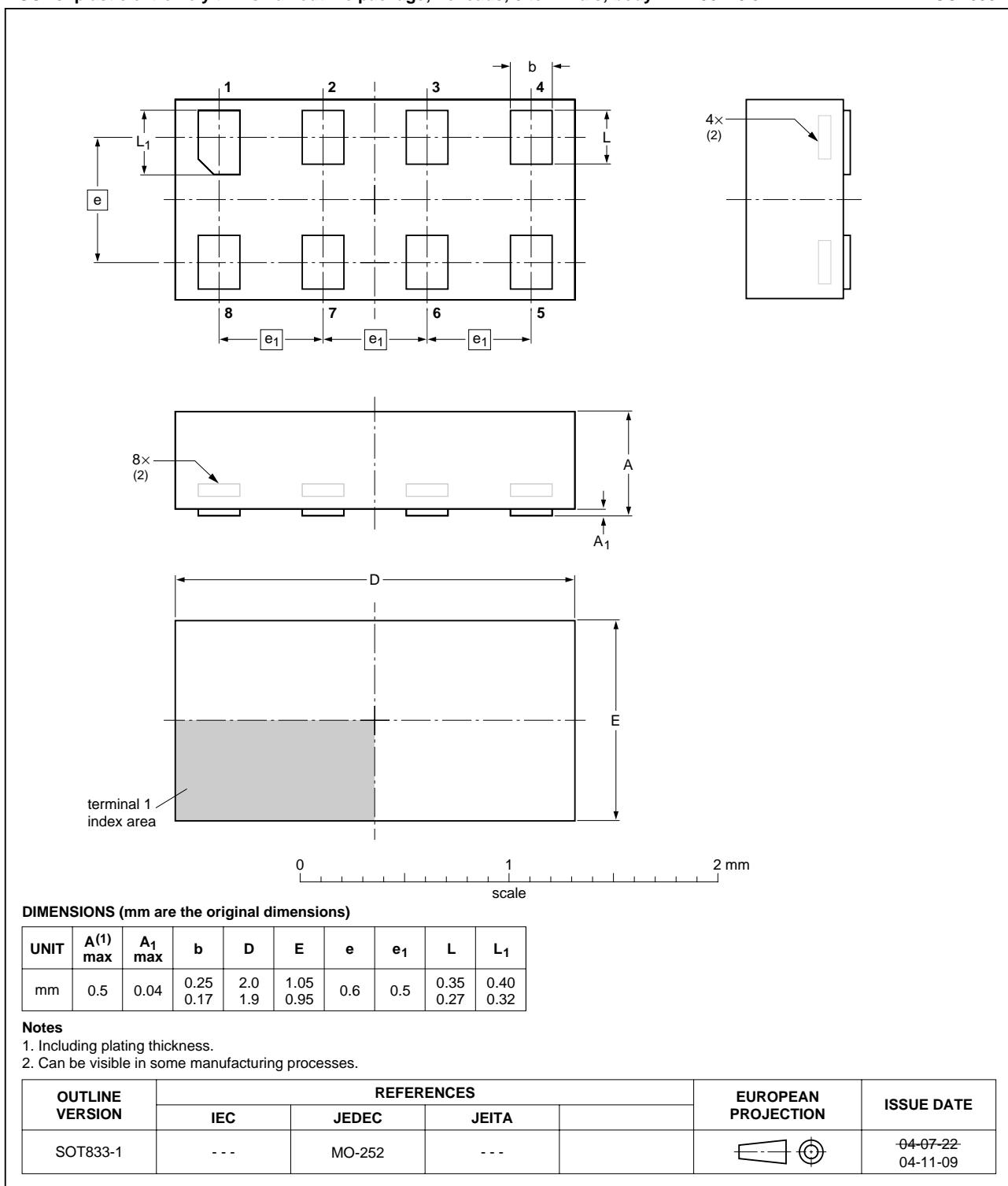
1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT765-1		MO-187			02-06-07

Fig 10. Package outline SOT765-1 (VSSOP8)

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm

SOT833-1

**Fig 11. Package outline SOT833-1 (XSON8)**

XQFN8: plastic extremely thin quad flat package; no leads; 8 terminals; body 1.6 x 1.6 x 0.5 mm

SOT902-1

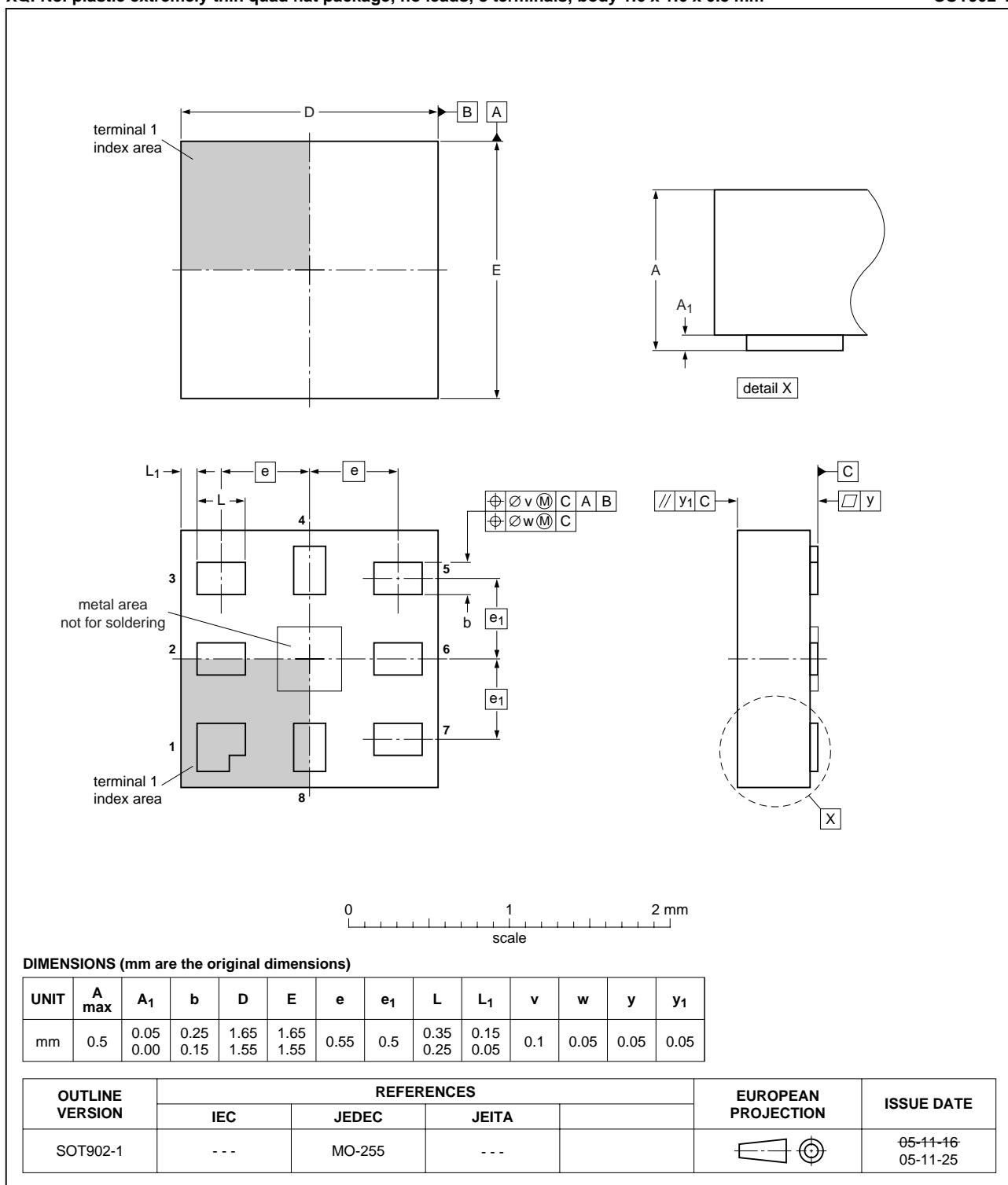


Fig 12. Package outline SOT902-1 (XQFN8)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC2G240_3	20071005	Product data sheet	-	74LVC2G240_2
Modifications:	<ul style="list-style-type: none"> The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. 			
74LVC2G240_2	20060728	Product data sheet	-	74LVC2G240_1
74LVC2G240_1	20030311	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

16.2 Definitions

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